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# 1 - 12 GHz Packaged Low-Noise MMIC Amplifier

**Satellite and Telemetry Communications** 

**Wide-band Communication Systems** 

**Commercial Wireless Systems** 

**Microwave Point-to-Point Radios** 

**APPLICATIONS** 

**Test Instrumentation** 

**EW Receiver Systems** 

#### **FEATURES**

Wideband: 1.0 to 12 GHz
 NF: 1.3 dB @ 2.0 GHz
 1.4 dB @ 6.0 GHz

1.9 dB @ 12.0 GHz

P-1dB: 16 dBm @ 6.0 GHz
 OIP3: 27 dBm @ 6.0 GHz
 Gain: 17 dB @ 6.0 GHz

• Bias Condition: VDD = 5 V

IDD = 55 mA

- 50-Ohm On-chip Matching
- Unconditionally Stable: 50 MHz to 20 GHz
- Gain Control Option Available with 2nd Gate Control Voltage
- 4x4 mm, 24 Lead Ceramic SMT Package

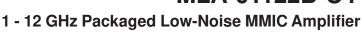
### **DESCRIPTION**

The MLA-01122B-C4 is a packaged fully-matched broadband Low-Noise MMIC amplifier utilizing high-reliability low-noise GaAs PHEMT technology. This MMIC is suited for Satellite Communications, Microwave radios, Instrumentation, Wideband Systems and also many commercial wireless applications where low-noise figure with high-gain is desirable. It has excellent gain (17 dB) and Noise Figure (1.4 dB, mid-band) over a broad frequency range. Typical P-1dB is 16 dBm and OIP3 is +27dBm @ 6 GHz. It has on-chip bias circuit, choke and DC blocking to provide bias stability and ease of use. The 2<sup>nd</sup> Gate voltage input can be used for gain control if necessary. Available in 4x4mm, 24 Lead Ceramic SMT Package.

# ELECTRICAL SPECIFICATIONS: VDD=+5.0V, VG1=+0.13V, VG2=+2V, IDD=55 mA, Ta=25 C, ZO=50 ohm (1)

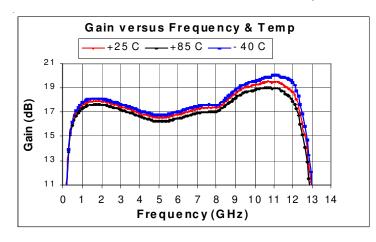
PARAMETER	TEST CONDITIONS	TYPICAL DATA	UNITS
Frequency Range		1-12	GHz
Gain	1 - 8 GHz 10 - 12 GHz	17 19	dB
Gain Flatness	1 - 8 GHz 1 - 12 GHz	0.7 1.5	+/-dB
Input Return Loss	2 GHz 5 GHz 10 GHz	15 9.5 13	dB
Output Return Loss		11	dB
Output P1dB	2 GHz 6 GHz 10 GHz 12 GHz	17.5 16.0 15.0 13.0	dBm
Output IP3 @ 0 dBm/tone, 1 MHz separation	2 GHz 6 GHz 12 GHz	30 27 25	dBm
Noise Figure	2 GHz 6 GHz 12 GHz	1.3 1.4 1.9	dB
Operating Bias Conditions: VDD IDD	VG1=+0.13V, VG2=+2V	+5 55	V m A
Stability Factor K	0.05 to 20 GHz	> 1	

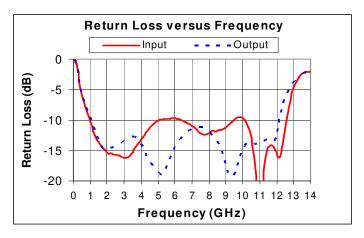
(1) All data is measured on Evaluation Board, with VG2 bias derived from VDD bias using resistive voltage divider as shown in Evaluation Board Schematic & Layout. (2) Vg1 can be slightly positive or negative depending on the lot and operation current.

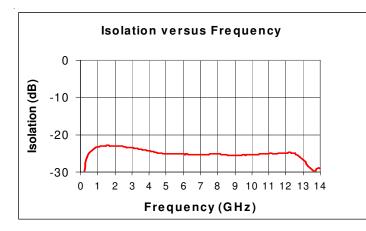


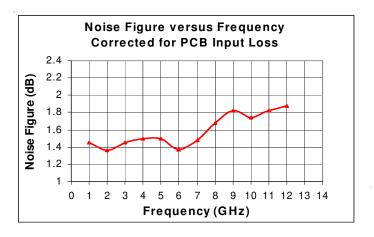


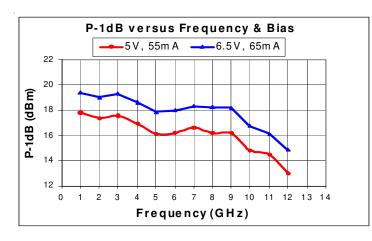
# TYPICAL RF PERFORMANCE: VDD=+5.0V, VG1=+0.13V, VG2=+2V, IDD=55 mA, Ta=25 C, ZO=50 ohm (1)

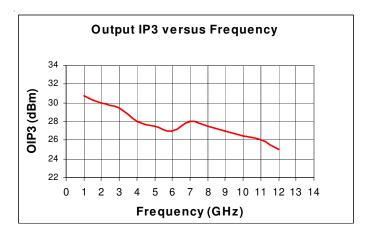








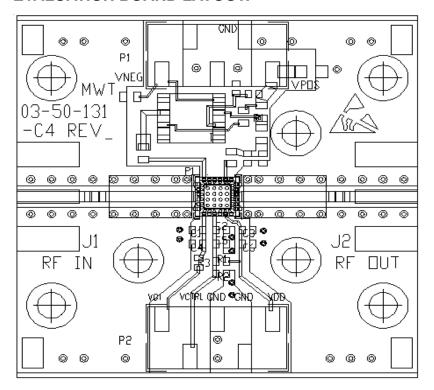








#### **EVALUATION BOARD LAYOUT:**



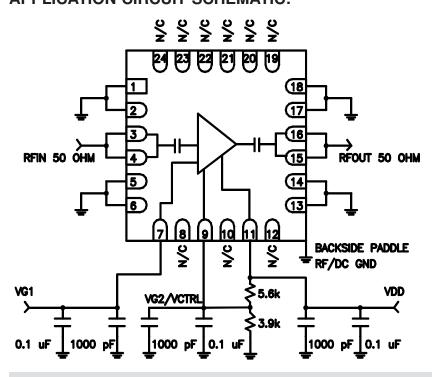
#### Parts List:

C1,C2,C3: 04025C102KAT2A 1000pF AVX
C4,C5,C8: 0402ZD104KAT2A 0.1uF AVX
R1: RK73B1ETTP562J(0402)5.6k AVX
R2: RK73B1ETTP392J(0402)3.9k AVX
R3: RK73Z1ETTP (0402)0 Ohms AVX
P2: TSM-105-01-S-SV SAMTEC
J1,J2:142-0701-841 JOHNSON
PCB: 20 mill thick 2-Layer R04003
Vias are plated & filled with Cupaste & planarized

#### NOTES:

1) BACKSIDE OF PACKAGE IS RF/DC GND AND MUST BE GROUNDED WITH ENOUGH VIAS AS SHOWN TO PCB RF/DC GND FOR BEST ELECTRICAL AND THERMAL PERFORMANCE

# **APPLICATION CIRCUIT SCHEMATIC:**

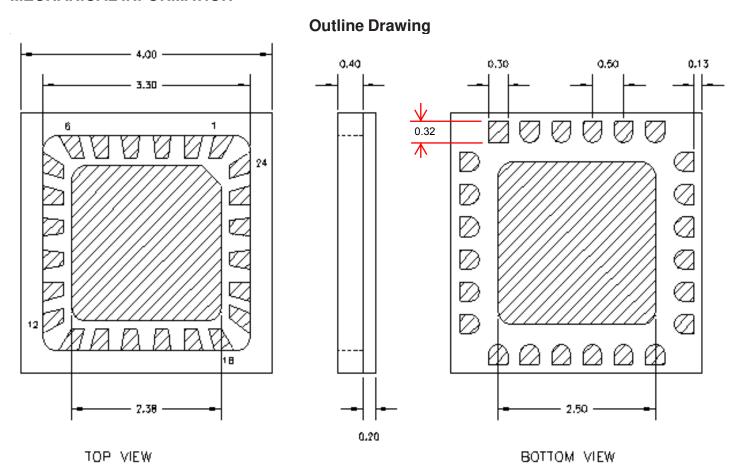


#### Notes:

- Package Backside is RF/DC GND and must be well grounded through PCB vias.
- External DC bypass capacitors must be placed as close to package as possible.



# **MECHANICAL INFORMATION**



### Notes:

- 1) 4X4 mm, 24 Lead Ceramic Package Outline Drawing.
- 2) Dimensions are in millimeters.
- 3) Lead and Ground Paddle Plating: Gold
- 4) Package Material: Black Alumina
- 5) All GND Leads and Backside Paddle must be grounded to PCB RF/DC ground.

# **ABSOLUTE MAXIMUM RATINGS**

SYMBOL	PARAMETERS	UNITS	MAX
VDD	Drain Voltage	V	7
IDD	Drain Current	mA	100
Pdiss	DC Pow er Dissipation	W	0.4
Pin max	RF Input Pow er	dBm	13
Toper	Operating Case/Lead Temp Range	ōC	-40 to +85
Tch	Channel Temperature	ōC	150
Tstg	Storage Temperature	<sup>o</sup> C	-60 to 150

Exceeding any on of these limits may cause permanent damage.

# **Functional Diagram**

